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Total Pages Sent 12

**IN THE UNITED STATES PATENT AND TRADEMARK OFFICE**

Applicant: Pan et al. Art Unit: 2812  
Serial No.: 10/669,111 Examiner: Pompey, R.  
Filing Date: 09/23/2003 Docket No.: TI-36040  
Customer No.: 23494 Conf. No.: 3098  
Title: DEPLETION DRAIN-EXTENDED MOS TRANSISTORS AND  
METHODS FOR MAKING THE SAME

**CERTIFICATION OF FACSIMILE TRANSMISSION**

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U.S. Patent and Trademark Office at 703-872-9306 on the date shown below:



Jacqueline J. Garner, Reg. No. 36,144

June 13, 2005  
Date

**FACSIMILE COVER SHEET**

<input checked="" type="checkbox"/> <b>FACSIMILE COVER SHEET</b>	<input checked="" type="checkbox"/> <b>AMENDMENT (8 Pages)</b>
<input type="checkbox"/> <b>NEW APPLICATION</b>	<input checked="" type="checkbox"/> <b>EOT 3mth (3 Pages)</b>
<input type="checkbox"/> <b>DECLARATION (# Pages)</b>	<input type="checkbox"/> <b>NOTICE OF APPEAL (# Pages)</b>
<input type="checkbox"/> <b>ASSIGNMENT (# Pages)</b>	<input type="checkbox"/> <b>APPEAL (# Pages)</b>
<input type="checkbox"/> <b>FORMAL DRAWINGS</b>	<input type="checkbox"/> <b>ISSUE FEE (# Pages)</b>
<input type="checkbox"/> <b>INFORMAL DRAWINGS</b>	<input type="checkbox"/> <b>REPLY BRIEF (IN TRIPLICATE) (# Pages)</b>
<input type="checkbox"/> <b>CONTINUATION APP'N (# Pages)</b>	
<input type="checkbox"/> <b>DIVISIONAL APP'N</b>	

<b>NAME OF INVENTOR(S):</b> Pan		<b>RECEIPT DATE &amp; SERIAL NO.:</b> <b>Serial No.: 10/669,111</b> <b>Filing Date: 9/23/2003</b> <b>Conf. No.: 3098</b>	
<b>TITLE OF INVENTION:</b> Depletion Drain-Extended . . .		<b>RECEIVED</b> <b>OIPE/IAP</b>  <b>JUN 14 2005</b>	
<b>TI FILE NO.:</b> <b>TI-36040</b>	<b>DEPOSIT ACCT. NO.:</b> <b>20-0668</b>		
<b>FAXED: 6/13/2005</b> <b>DUE: 3/13/2005</b> <b>ATTY/SEC'Y: JJG</b>			

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Applicant:	Pan et al.	Art Unit:	2812
Serial No.:	10/669,111	Examiner:	Pompey, R.
Filing Date:	09/23/2003	Docket No.:	TI-36040
Customer No.:	23494	Conf. No.:	3098
Title: DEPLETION DRAIN-EXTENDED MOS TRANSISTORS AND METHODS FOR MAKING THE SAME			

## AMENDMENT UNDER 37 CFR 1.111

Commissioner for Patents  
P.O. Box 1450  
Alexandria, VA 22313-1450

## CERTIFICATION OF FACSIMILE TRANSMISSION

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transmitted by facsimile to the U.S. Patent and  
Trademark Office at (703) 872 - 9306 on 6/13/2005.

  
Jacqueline J. Garner  
Reg. No. 36,144

Dear Sir:

The following amendments and remarks are offered in response to the Examiner's Office Action dated 12/13/2004. They are respectfully submitted as a full and complete response to that Action.

Please amend the above-referenced application as follows:

There are no **Amendments to the Specification**.

**Amendments to the Claims** are reflected in the listing of claims that begin on page 2 of this paper.

There are no **Amendments to the Drawings**.

The **Remarks** begin on page 6.